a gate electrode overlapping with the channel forming regions and some of the impurity regions, with a gate insulating film interposed therebetween,

wherein said some of the impurity regions are located between the plurality of channel regions in the semiconductor film, and

wherein a thickness of a gate insulating film of a TFT in said driver circuit portion is thinner than that of the gate insulating film of a TFT in the pixel portion.

C1 amend

4. (Amended) A display device comprising a pixel portion and a driver circuit portion on a substrate, said pixel portion comprising:

a semiconductor film comprising a plurality of channel forming regions, a plurality of impurity regions, a source region, and a drain region; and

a gate electrode overlapping with the channel forming regions and some of the impurity regions, with a gate insulating film interposed therebetween,

wherein said some of the impurity regions are located between the plurality of channel regions in the semiconductor film, and

wherein a gate insulating film of a TFT in said driver circuit portion and a dielectric of a storage capacitor formed in said pixel portion comprise the same material and have the same film thickness.

C2

5. (Amended) An electronic equipment comprising a display device according to claim 3, wherein said electronic equipment is selected from the group consisting of a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a notebook type personal computer, a game machine, a portable information terminal, a mobile computer, a portable telephone, a portable game machine, an electronic book, and an image reproduction devices having recording medium.

C3

6. (Amended) A device according to claim 3, wherein said plurality of impurity regions comprise a plurality of low concentration impurity regions, a high concentration impurity region,

C3

and wherein said some of the low concentration impurity regions and the high concentration impurity region are located between the plurality of the channel regions in the semiconductor film.

8. (Amended) A device according to claim 4, wherein said plurality of impurity regions comprise a plurality of low concentration impurity regions, a high concentration impurity region, and wherein said some of the low concentration impurity regions and the high concentration impurity region are located between the plurality of the channel regions in the semiconductor film..

C4

9. (Amended) A device according to claim 4, wherein at least two of said impurity regions overlapped with the gate electrode contain an element at a concentration of 2×10^{16} to 5×10^{19} atoms/cm^3, and at least one of the impurity regions overlapped with the gate electrode contain the element at a concentration of 5×10^{19} to 3×10^{21} atoms/cm^3.

C5

10. (Amended) An electronic equipment comprising a display device according to claim 4, wherein said electronic equipment is selected from the group consisting of a video camera, a digital camera, a projector, a projection TV, a goggle type displays, a navigation system, a sound reproduction device, a notebook type personal computer, a game machine, a portable information terminal, a mobile computer, a portable telephone, a portable game machine, an electronic books, and an image reproduction devices having recording medium.

C6

16. (Amended) A display device comprising a pixel portion and a driver circuit portion on a substrate, said pixel portion comprising:

a semiconductor film comprising at least two channel forming regions, at least one first impurity region, at least one second impurity region, a source region, and a drain region; and

a gate electrode overlapped with said two channel forming regions and the first impurity region, and a part of the second impurity region with a gate insulating film interposed therebetween,

C6

wherein one of channel forming regions is located between the first impurity region and the second impurity region,

wherein a thickness of a gate insulating film of a thin film transistor in said driver circuit portion is thinner than that of the gate insulating film in the pixel portion.

C7

17. (Amended) An electronic equipment comprising a display device according to claim 16, wherein said electronic equipment is selected from the group consisting of a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a notebook type personal computer, a game machine, a portable information terminal, a mobile computer, a portable telephone, a portable game machine, an electronic book, and an image reproduction devices having recording medium.

C8

18. (Amended) A display device comprising a pixel portion and a driver circuit portion on a substrate, said pixel portion comprising:

a semiconductor film having at least two channel forming regions, first and second low concentration impurity regions, a high concentration impurity regions, a source region, and a drain region; and

a gate electrode overlapping with said two channel forming regions, the first low concentration impurity regions, the high concentration impurity region, and portions of the second impurity regions, with a gate insulating film interposed therebetween,

wherein the high concentration impurity region is located between the channel forming regions, and

wherein said driver circuit portion includes a TFT including a gate insulating film, and said pixel portion includes a storage capacitor including a dielectric, said gate insulating film of said TFT and said dielectric of said storage capacitor comprising the same material and having the same film thickness.

C9

21. (Amended) A device according to claim 3, wherein the impurity regions have the same conductivity as the source and drain regions.

22. (Amended) A device according to claim 9, wherein the element belongs to group XV in the periodic table.

23. (Amended) A device according to claim 4, wherein the impurity regions have the same conductivity as the source and drain regions.

26. (Amended) A device according to claim 16, wherein the first and second impurity regions have the same conductivity as the source and drain regions.

C10

27. (Amended) A device according to claim 16, wherein each of the first and second impurity region contains an at a concentration of 2×10^{16} to 5×10^{19} atoms/cm^3, and

wherein the semiconductor film further comprises a third impurity region including the element at a concentration of 5×10^{19} to 3×10^{21} atoms/cm^3.

C11

29. (Amended) A device according to claim 16, wherein a gate insulating film of a TFT in said driver circuit portion and a dielectric of a storage capacitor formed in said pixel portion comprise the same material and have the same film thickness.